Transistor

4V Drive Pch MOS FET

RSS070P05

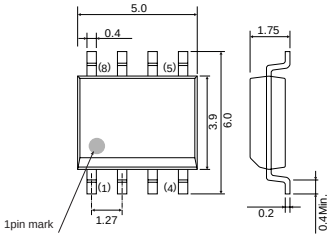
●Structure
Silicon P-channel
MOS FET

●Features
1) Built-in G-S Protection Diode.
2) Small and Surface Mount Package (SOP8).

●Applications
Power switching , DC / DC converter , Inverter

●External dimensions (Unit : mm)

SOP8



Each lead has same dimensions

●Packaging dimensions

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS070P05		○

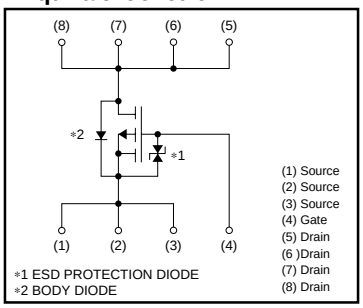
●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-45	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±7.0	A
	Pulsed	I_{DP} *1	±28	A
Source current (Body diode)	Continuous	I_S	-1.6	A
	Pulsed	I_{SP} *1	-28	A
Total power dissipation		P_D *2	2	W
Chanel temperature		T_{ch}	150	°C
Range of Storage temperature		T_{stg}	-55 to +150	°C

*1 PW≤10μs、Duty cycle≤1%

*2 Mounted on a ceramic board

●Equivalent circuit



●Thermal resistance

Parameter	Symbol	Limits	Unit
Chanel to ambient	$R_{th(ch-a)}$ *	62.5	°C/W

* Mounted on a ceramic board

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	–45	–	–	V	I_D= –1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}= –45V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–1.0	–	–2.5	V	V_{DS}= –10V, I_D= –1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	19	27	mΩ	I_D= –7A, V_{GS}= –10V
		–	25	35	mΩ	I_D= –7A, V_{GS}= –4.5V
		–	28	39	mΩ	I_D= –7A, V_{GS}= –4.0V
Forward transfer admittance	$\|Y_{fs}\|$ *	10.0	–	–	S	V_{DS}= –10V, I_D= –7A
Input capacitance	C_{iss}	–	4100	–	pF	V_{DS}= –10V
Output capacitance	C_{oss}	–	510	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	330	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	31	–	ns	V_{DD}≒ –25V I_D= –3.5A V_{GS}= –10V R_L=–7Ω R_G=10Ω
Rise time	t_r *	–	35	–	ns	
Turn-off delay time	$t_{d\ (off)}$ *	–	135	–	ns	
Fall time	t_f *	–	50	–	ns	
Total gate charge	Q_g *	–	34.0	47.6	nC	V_{DD}≒ –25V V_{GS}= –5V
Gate-source charge	Q_{gs} *	–	9.5	–	nC	I_D= –7A
Gate-drain charge	Q_{gd} *	–	12	–	nC	R_L=3.5Ω R_G=10Ω

*Pulsed

Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	–	–	–1.2	V	I_S= –7A, V_{GS}=0V

*Pulsed

●**Electrical characteristic curves**

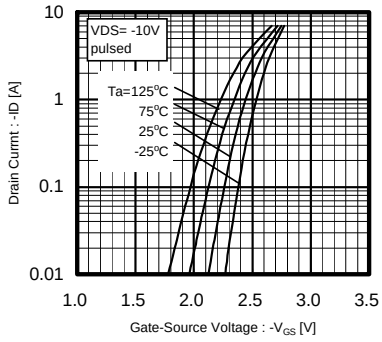


Fig.1 Typical Transfer Characteristics

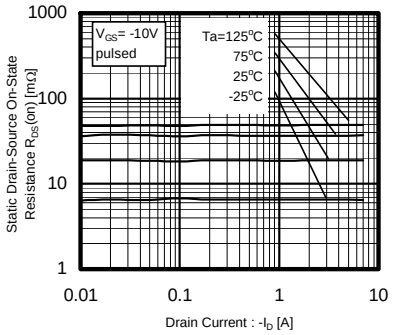


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

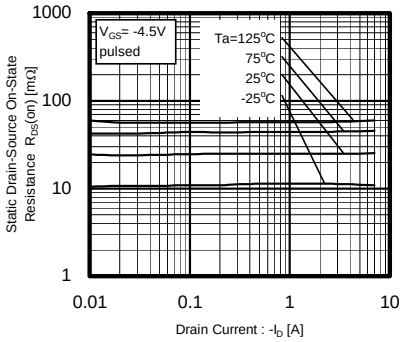


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

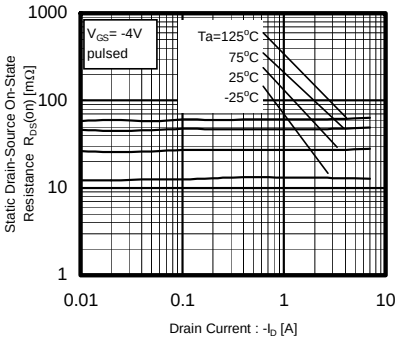


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

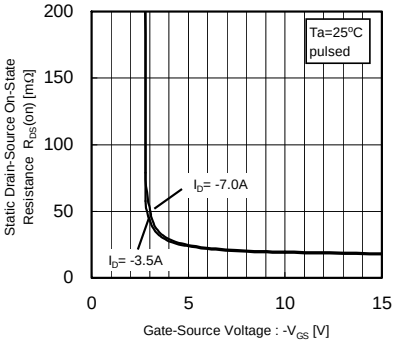


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

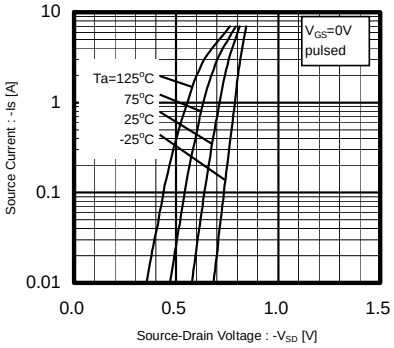


Fig.6 Source-Current vs. Source-Drain Voltage

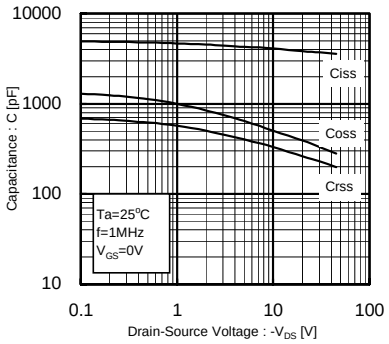


Fig.7 Typical capacitance vs. Source-Drain Voltage

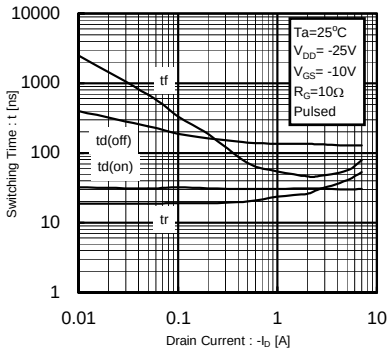


Fig.8 Switching Characteristics

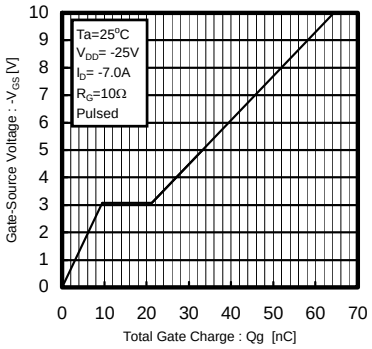


Fig.9 Dynamic Input Characteristics

●**Measurement circuits**

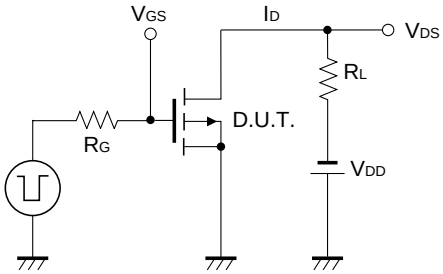


Fig.10 Switching Time Test Circuit

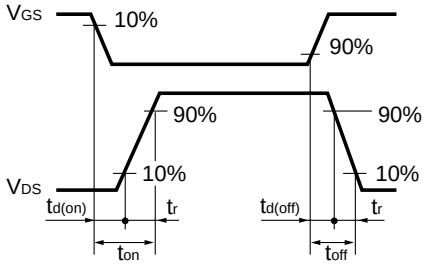


Fig.11 Switching Time Waveforms

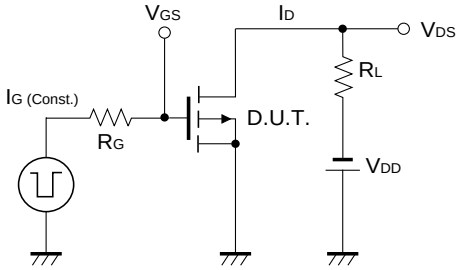


Fig.12 Gate Charge Test Circuit

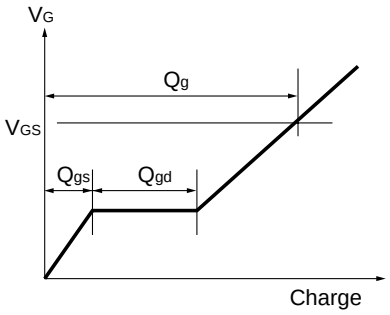


Fig.13 Gate Charge Waveform

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